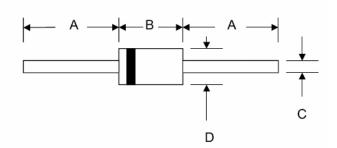
SF21-SF27 2.0A SUPER- FAST RECTIFIER

Technical Data Data Sheet N1020, Rev. - **Green Products**

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



Mechanical Data

Case: Molded Plastic

Epoxy: Device has flammability classification 94-O
 Lead: MIL-STD-202E method 208C guaranteed

Mounting Position: Any

Weight: 0.35 gram

DO-15								
Dim	Min	Max	Min	Max				
Α	25.4	_	1.000	_				
В	5.50	7.62	0.217	0.300				
С	0.71	0.864	0.028	0.034				
D	2.60	3.60	0.102	0.142				
	In mm		In inch					

Marking Diagram:

Where XXXXX is YYWWL



SF21 = Part Name
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
SF21-SF27	DO-15(Pb-Free)	3000pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

[•] Weiqi Street, Airport Development Zone, Jiangning District, Nanjing, China 211113 🗏 (86) 25-87123907 •

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Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SF21	SF22	SF23	SF24	SF25	SF26	SF27	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	50	100	150	200	300	400	600	V
RMS Reverse Voltage	VR(RMS)	35	70	105	140	210	280	420	V
Average Rectified Output Current (Note 1) @T _A = 55°C	lo	2.0						Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I	50						Α	
Forward Voltage @I _F = 2.0A	VFM	0.95 1.3			1.7	V			
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I IRM	5.0 100						μА	
Reverse Recovery Time (Note 2)	trr	35						nS	
Typical Junction Capacitance (Note 3)	Cj	60 30					pF		
Operating Temperature Range	Tj	-65 to +125						°C	
Storage Temperature Range	Тѕтс	-65 to +150						°C	

*Glass passivated forms are available upon request

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

- 2. Measured with IF = 0.5A, IR = 1.0A, IRR = 0.25A. See figure 5.
- 3. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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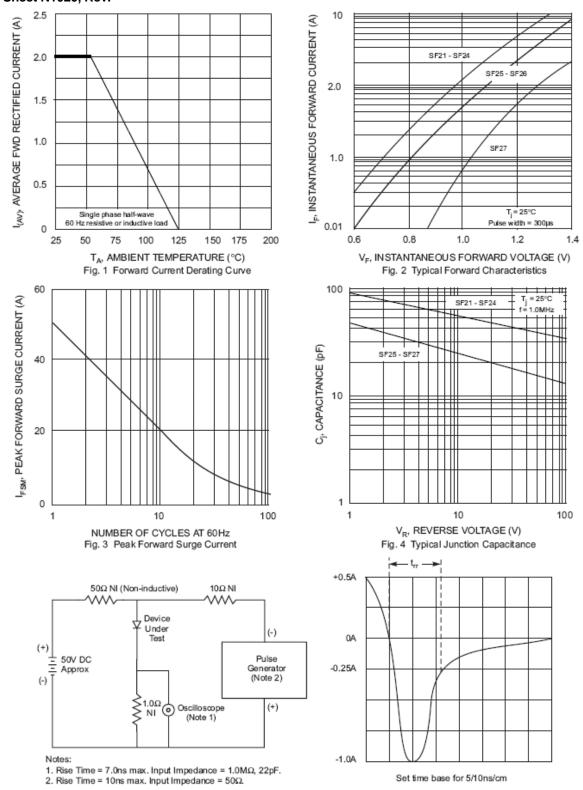


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit

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